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(54) Title (EN): OXIDE SEMICONDUCTOR SUBSTRATE AND SCHOTTKY BARRIER DIODE

(54) Title (FR): SUBSTRAT SEMICONDUCTEUR À OXYDE ET DIODE À BARRIÈRE DE SCHOTTKY

(54) Title (JA): 酸化物半導体基板及びショットキーバリアダイオード

(57) Abstract:
(EN): A Schottky barrier diode element having a silicon (Si) substrate, an oxide semiconductor layer, and a Schottky electrode layer, wherein the oxide semiconductor layer contains a polycrystalline and/or amorphous oxide semiconductor having a band gap of 3.0-5.6 eV, inclusive.

(FR): L'invention concerne un élément diode à barrière de Schottky comprenant un substrat en silicium (Si), une couche d'oxyde semiconductrice et une couche d'électrode de Schottky, la couche d'oxyde semiconductrice contenant un semiconducteur à oxyde polycristallin et/ou amorphe ayant une largeur de bande interdite de 3,0 à 5,6 eV y compris.

(JA): シリコン(Ｓｉ)基板と、酸化物半導体層と、ショットキー電極層とを有するショットキーバリアダイオード素子であって、前記酸化物半導体層が、３．０ｅＶ以上、５．６ｅＶ以下のバンドギャップを有する多結晶及び／又は非晶質の酸化物半導体を含むショットキーバリアダイオード素子。

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